

# IR2110E4

## HIGH AND LOW SIDE DRIVER

### Features

- Floating channel designed for bootstrap operation  
 Fully operational to +400V  
 Tolerant to negative transient voltage  
 dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- Separate logic supply range from 5 to 20V  
 Logic and power ground  $\pm 5V$  offset
- CMOS Schmitt-triggered inputs with pull-down
- Cycle by cycle edge-triggered shutdown logic
- Matched propagation delay for both channels
- Outputs in phase with inputs

### Product Summary

<b>V<sub>OFFSET</sub></b>	<b>400V max.</b>
<b>I<sub>O+/-</sub></b>	<b>2A / 2A</b>
<b>V<sub>OUT</sub></b>	<b>10 - 20V</b>
<b>t<sub>on/off</sub> (typ.)</b>	<b>120ns &amp; 94ns</b>
<b>Delay Matching</b>	<b>10ns</b>

### Description

The IR2110E4 is a high voltage, high speed power MOSFET and IGBT driver with independent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. Logic inputs are compatible with standard CMOS or LSTTL outputs. The output drivers

feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays are matched to simplify use in high frequency applications. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 400 volts.

### Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions. Additional information is shown in Figures 28 through 35.

Symbol	Parameter	Min.	Max.	Units
V <sub>B</sub>	High Side Floating Supply Absolute Voltage	-0.5	V <sub>S</sub> + 20	V
V <sub>S</sub>	High Side Floating Supply Offset Voltage	—	400	
V <sub>HO</sub>	High Side Output Voltage	V <sub>S</sub> - 0.5	V <sub>B</sub> + 0.5	
V <sub>CC</sub>	Low Side Fixed Supply Voltage	-0.5	20	
V <sub>LO</sub>	Low Side Output Voltage	-0.5	V <sub>CC</sub> + 0.5	
V <sub>DD</sub>	Logic Supply Voltage	-0.5	V <sub>SS</sub> + 20	
V <sub>SS</sub>	Logic Supply Offset Voltage	V <sub>CC</sub> - 20	V <sub>CC</sub> + 0.5	
V <sub>IN</sub>	Logic Input Voltage (HIN, LIN & SD)	V <sub>SS</sub> - 0.5	V <sub>DD</sub> + 0.5	
dV <sub>S</sub> /dt	Allowable Offset Supply Voltage Transient (Fig. 16)	—	50	V/ns
P <sub>D</sub>	Package Power Dissipation @ T <sub>A</sub> ≤ 25°C (Fig. 19)	—	1.6	W
R <sub>thJA</sub>	Thermal Resistance, Junction to Ambient	—	125	°C/W
T <sub>J</sub>	Junction Temperature	-55	125	°C
T <sub>S</sub>	Storage Temperature	-55	150	
T <sub>L</sub>	Package Mounting Surface Temperature	300 (for 5 seconds)		
	Weight	0.45 (typical)		g

## Recommended Operating Conditions

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. The  $V_S$  and  $V_{SS}$  offset ratings are tested with all supplies biased at 15V differential. Typical ratings at other bias conditions are shown in Figures 36 and 37.

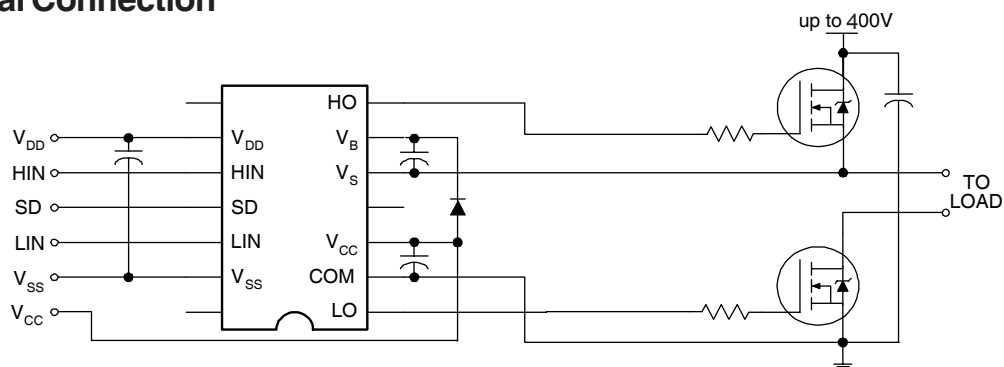
Symbol	Parameter	Min.	Max.	Units
$V_B$	High Side Floating Supply Absolute Voltage	$V_S + 10$	$V_S + 20$	V
$V_S$	High Side Floating Supply Offset Voltage	-4	400	
$V_{HO}$	High Side Output Voltage	$V_S$	$V_B$	
$V_{CC}$	Low Side Fixed Supply Voltage	10	20	
$V_{LO}$	Low Side Output Voltage	0	$V_{CC}$	
$V_{DD}$	Logic Supply Voltage	$V_{SS} + 5$	$V_{SS} + 20$	
$V_{SS}$	Logic Supply Offset Voltage	-5	5	
$V_{IN}$	Logic Input Voltage (HIN, LIN & SD)	$V_{SS}$	$V_{DD}$	

## Dynamic Electrical Characteristics

$V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ,  $V_{DD}$ ) = 15V,  $C_L$  = 1000 pF,  $T_A$  = 25°C and  $V_{SS}$  = COM unless otherwise specified. The dynamic electrical characteristics are measured using the test circuit shown in Figure 3.

Symbol	Parameter	$T_j = 25^\circ\text{C}$			$T_j = -55$ to $125^\circ\text{C}$		Units	Test Conditions
		Min	Typ.	Max.	Min.	Max.		
$t_{on}$	Turn-On Propagation Delay	—	120	150	—	260	nS	$V_S = 0\text{V}$
$t_{off}$	Turn-Off Propagation Delay	—	94	125	—	220		$V_S = 400\text{V}$
$t_{sd}$	Shutdown Propagation Delay	—	110	140	—	235		$V_S = 400\text{V}$
$t_r$	Turn-On Rise Time	—	25	35	—	50		$C_L = 1000\text{pF}$
$t_f$	Turn-Off Fall Time	—	17	25	—	40		$C_L = 1000\text{pF}$
Mt	Delay Matching, HS & LS Turn-On/Off	—	—	20	—	—		$ H_{t_{on}} - L_{t_{on}}  /  H_{t_{off}} - L_{t_{off}} $

## Typical Connection



### Static Electrical Characteristics

VBIAS (VCC, VBS, VDD) = 15V, TA = 25°C and VSS = COM unless otherwise specified. The VIN, VTH and IIN parameters are referenced to VSS and are applicable to all three logic input leads: HIN, LIN and SD. The VO and IO parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Symbol	Parameter	Tj = 25°C			Tj = -55 to 125°C		Units	Test Conditions	
		Min	Typ.	Max.	Min.	Max.			
V <sub>IH</sub>	Logic "1" Input Voltage	9.5	—	—	10	—	V	V <sub>DD</sub> = 15V	
V <sub>IL</sub>	Logic "0" Input Voltage	—	—	6	—	5.7		V <sub>DD</sub> = 15V	
V <sub>OH</sub>	High Level Output Voltage, V <sub>BIAS</sub> - V <sub>O</sub>	—	0.7	1.2	—	1.5		V <sub>IN</sub> = V <sub>IH</sub> , I <sub>O</sub> = 0A	
V <sub>OL</sub>	Low Level Output Voltage, V <sub>O</sub>	—	—	0.1	—	0.1		V <sub>IN</sub> = V <sub>IL</sub> , I <sub>O</sub> = 0A	
I <sub>LK</sub>	Offset Supply Leakage Current	—	—	50	—	250	μA	V <sub>B</sub> = V <sub>S</sub> = 400V	
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> Supply Current	—	125	230	—	500		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	
I <sub>QCC</sub>	Quiescent V <sub>CC</sub> Supply Current	—	180	340	—	600		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	
I <sub>QDD</sub>	Quiescent V <sub>DD</sub> Supply Current	—	5	30	—	60		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	
I <sub>IN+</sub>	Logic "1" Input Bias Current	—	15	40	—	70		V <sub>IN</sub> = 15V	
I <sub>IN-</sub>	Logic "0" Input Bias Current	—	—	1	—	10		V <sub>IN</sub> = 0V	
V <sub>B<sub>SUV+</sub></sub>	V <sub>BS</sub> Supply Undervoltage Positive Going Threshold	7.5	8.7	9.7	—	—		V	
V <sub>B<sub>SUV-</sub></sub>	V <sub>BS</sub> Supply Undervoltage Negative Going Threshold	7.0	8.3	9.4	—	—			
V <sub>C<sub>CUV+</sub></sub>	V <sub>CC</sub> Supply Undervoltage Positive Going Threshold	7.4	8.6	9.6	—	—			
V <sub>C<sub>CUV-</sub></sub>	V <sub>CC</sub> Supply Undervoltage Negative Going Threshold	7.0	8.2	9.4	—	—			
I <sub>O+</sub>	Output High Short Circuit Pulsed Current	2	—	—	—	—	A	V <sub>OUT</sub> = 0V, V <sub>IN</sub> = 15V PW <= 10μs	
I <sub>O-</sub>	Output Low Short Circuit Pulsed Current	2	—	—	—	—		V <sub>OUT</sub> = 15V, V <sub>IN</sub> = 0V PW <= 10μs	

# IR2110E4

International  
**IR** Rectifier

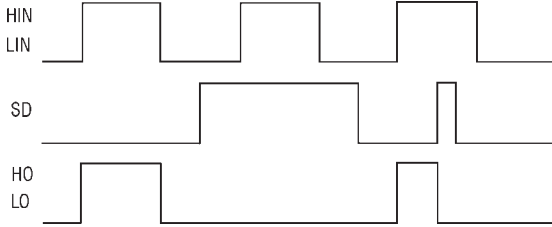


Figure 1. Input/Output Timing Diagram

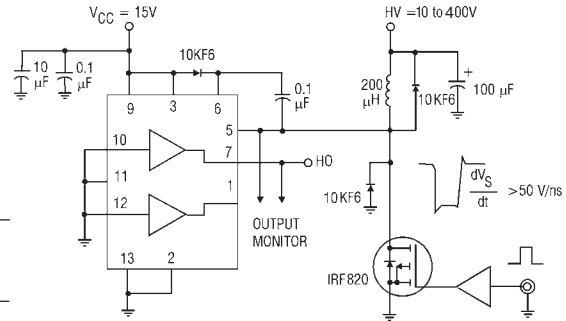


Figure 2. Floating Supply Voltage Transient Test Circuit

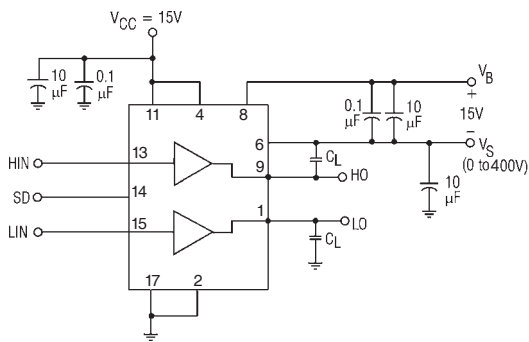


Figure 3. Switching Time Test Circuit

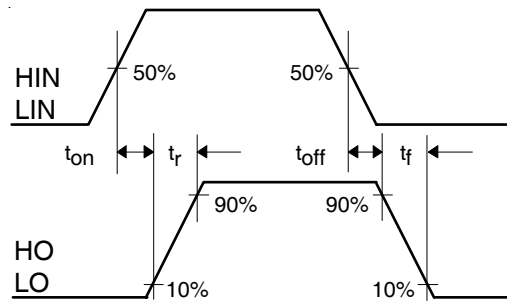


Figure 4. Switching Time Waveform Definition

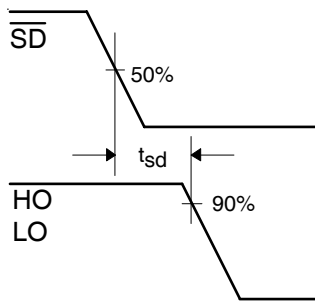


Figure 3. Shutdown Waveform Definitions

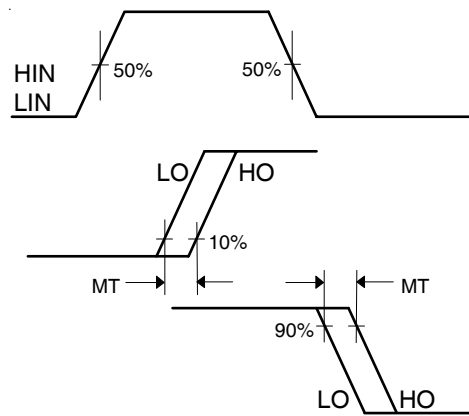


Figure 6. Delay Matching Waveform Definitions

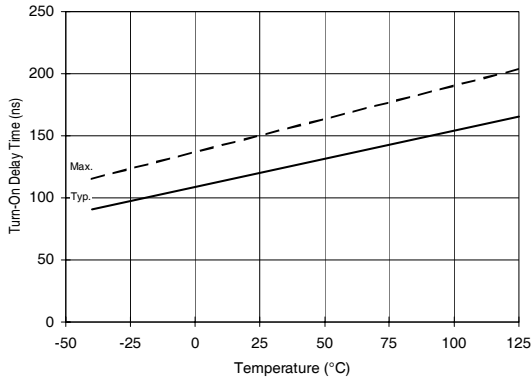


Figure 7A. Turn-On Time vs. Temperature

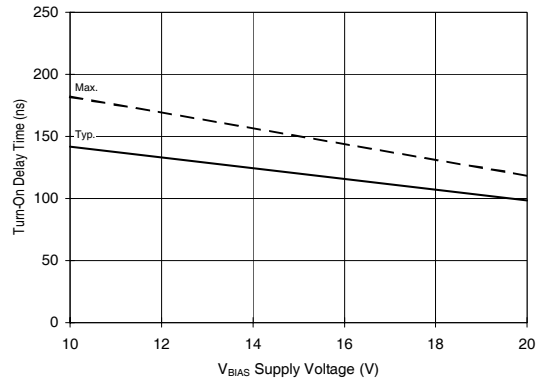


Figure 7B. Turn-On Time vs. Voltage

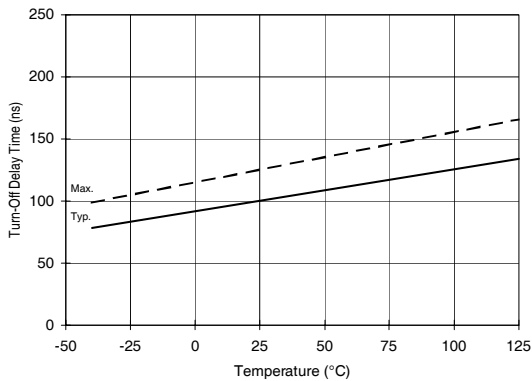


Figure 8A. Turn-Off Time vs. Temperature

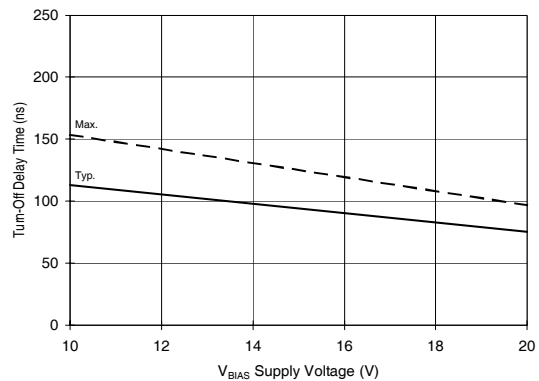


Figure 8B. Turn-Off Time vs. Voltage

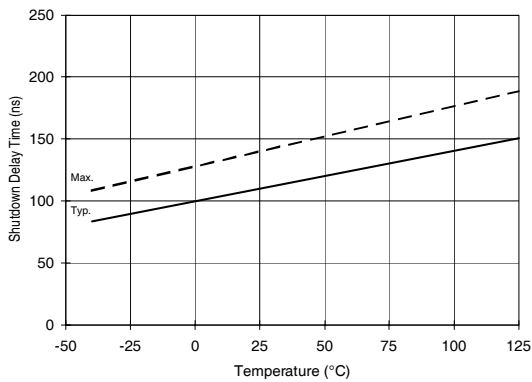


Figure 9A. Shutdown Time vs. Temperature

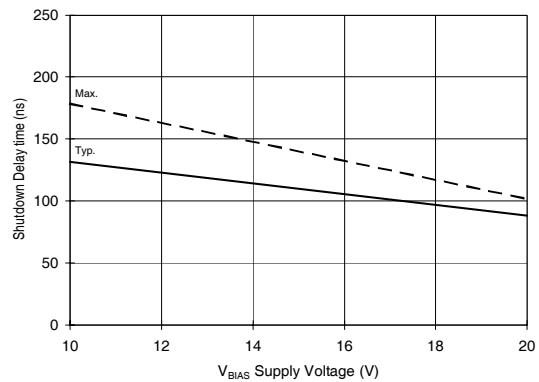


Figure 9B. Shutdown Time vs. Voltage

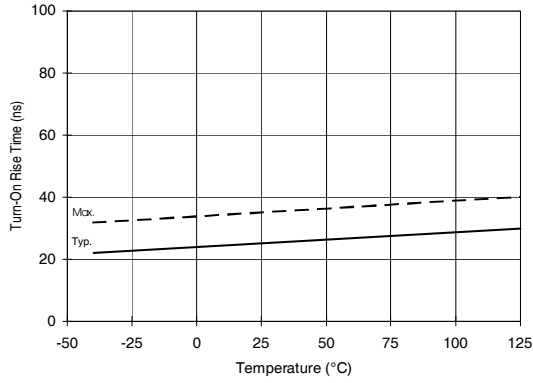


Figure 10A. Turn-On Rise Time vs. Temperature

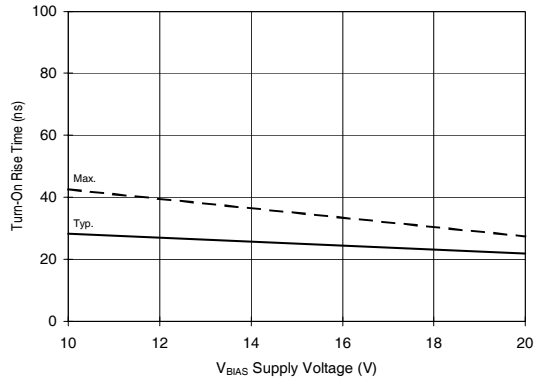


Figure 10B. Turn-On Rise Time vs. Voltage

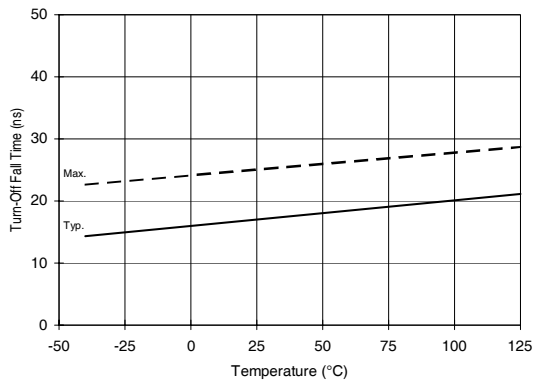


Figure 11A. Turn-Off Fall Time vs. Temperature

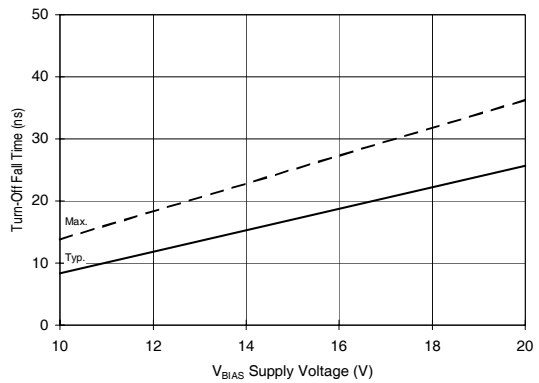


Figure 11B. Turn-Off Fall Time vs. Voltage

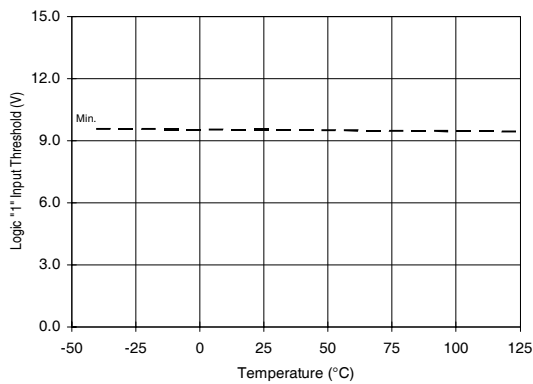


Figure 12A. Logic "1" Input Threshold vs. Temperature

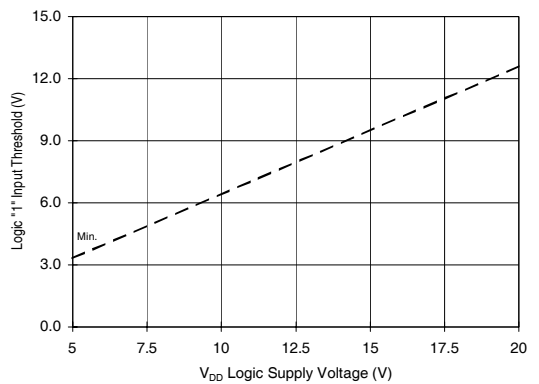


Figure 12B. Logic "1" Input Threshold vs. Voltage

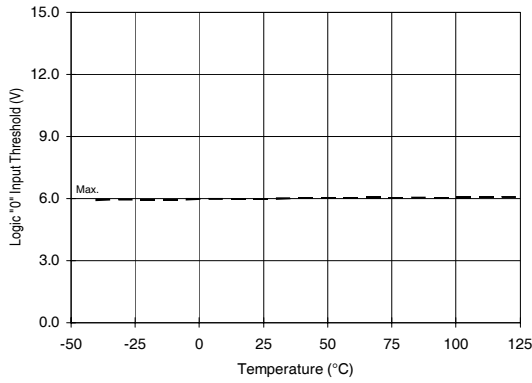


Figure 13A. Logic "0" Input Threshold vs. Temperature

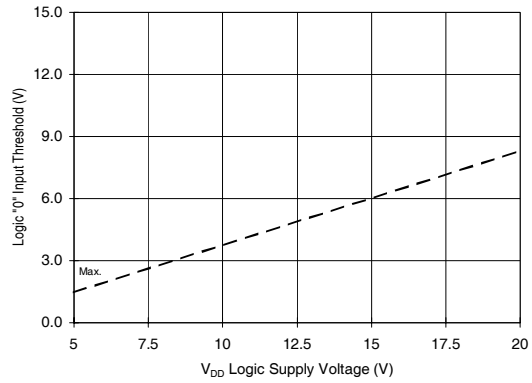


Figure 13B. Logic "0" Input Threshold vs. Voltage

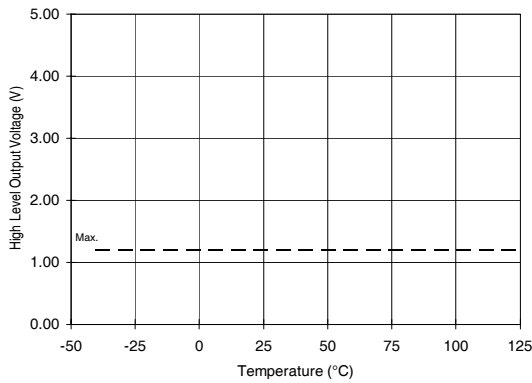


Figure 14A. High Level Output vs. Temperature

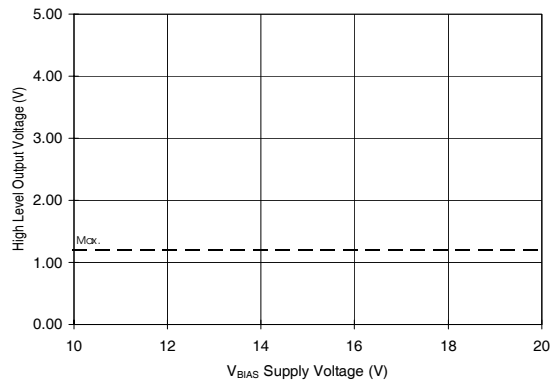


Figure 14B. High Level Output vs. Voltage

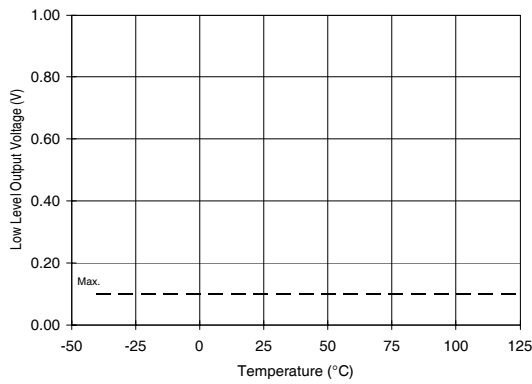


Figure 15A. Low Level Output vs. Temperature

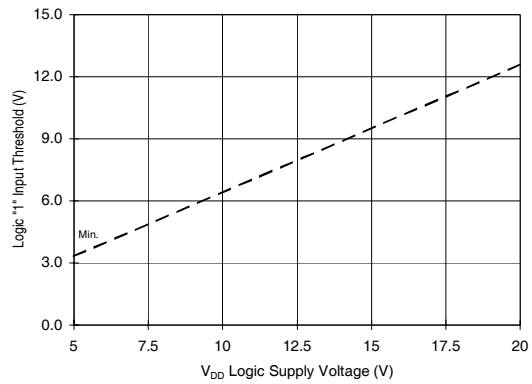


Figure 15B. Low Level Output vs. Voltage

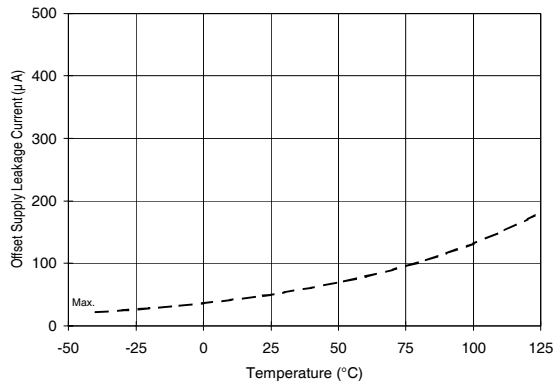


Figure 16A. Offset Supply Current vs. Temperature

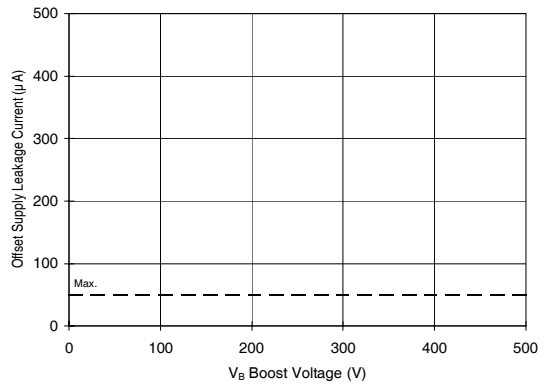


Figure 16B. Offset Supply Current vs. Voltage

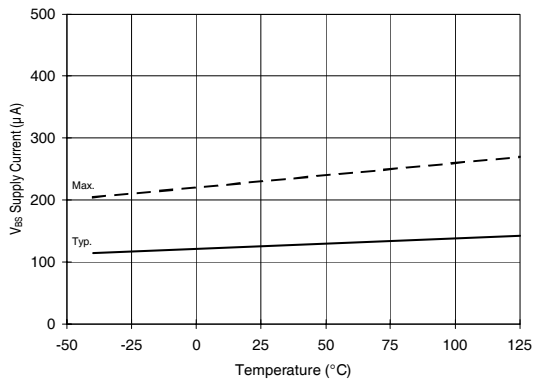


Figure 17A. V<sub>BS</sub> Supply Current vs. Temperature

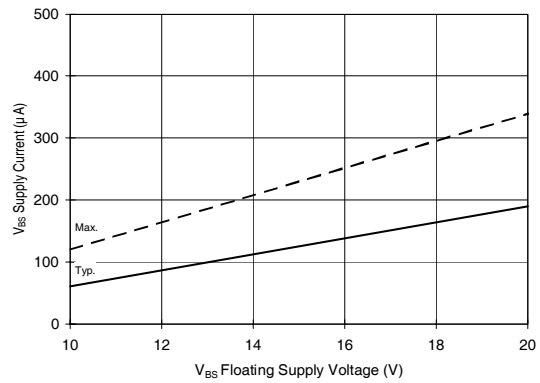


Figure 17B. V<sub>BS</sub> Supply Current vs. Voltage

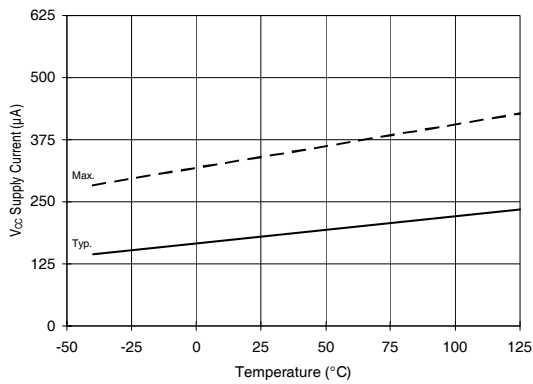


Figure 18A. V<sub>CC</sub> Supply Current vs. Temperature

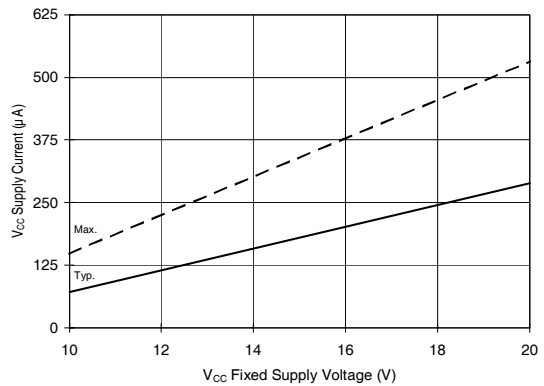


Figure 18B. V<sub>CC</sub> Supply Current vs. Voltage



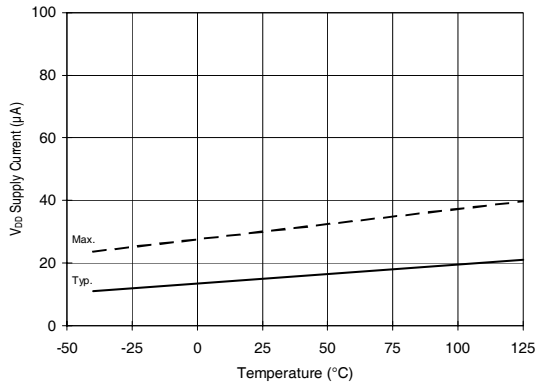


Figure 19A.  $V_{DD}$  Supply Current vs. Temperature

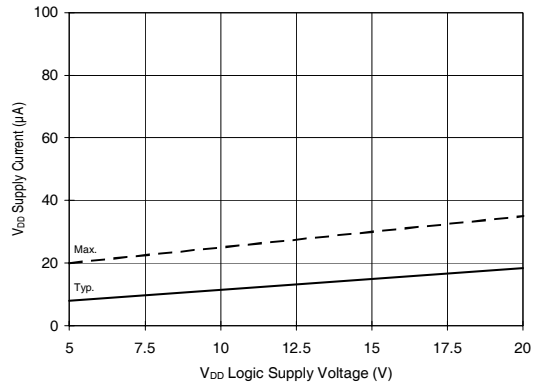


Figure 19B.  $V_{DD}$  Supply Current vs. Voltage

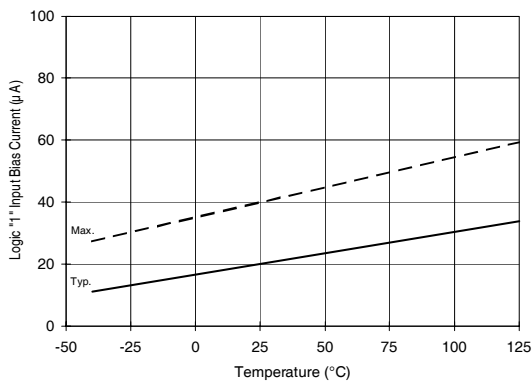


Figure 20A. Logic "1" Input Current vs. Temperature

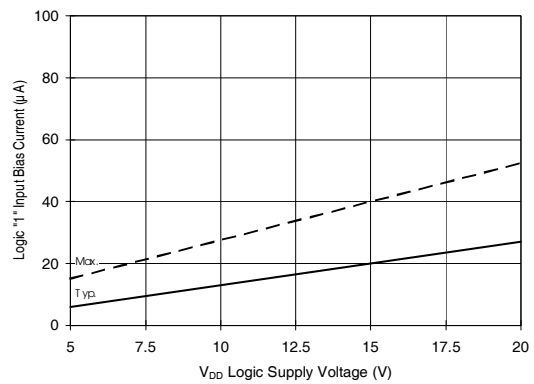


Figure 20B. Logic "1" Input Current vs. Voltage

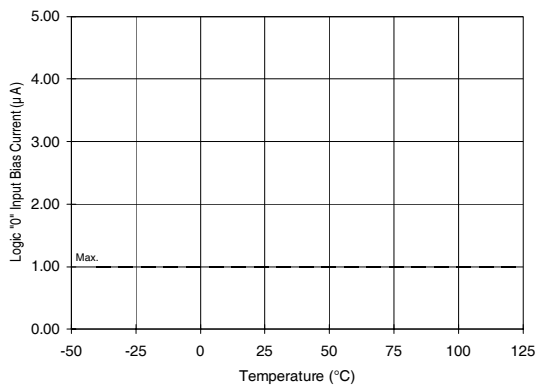


Figure 21A. Logic "0" Input Current vs. Temperature

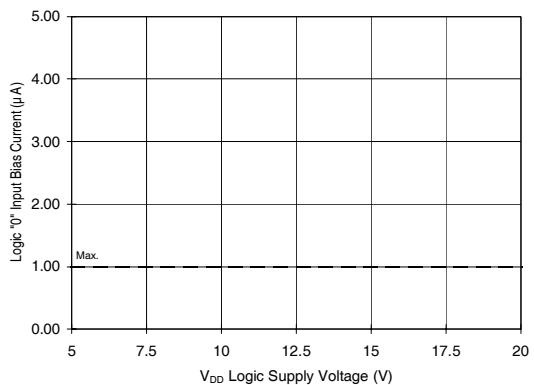


Figure 21B. Logic "0" Input Current vs. Voltage

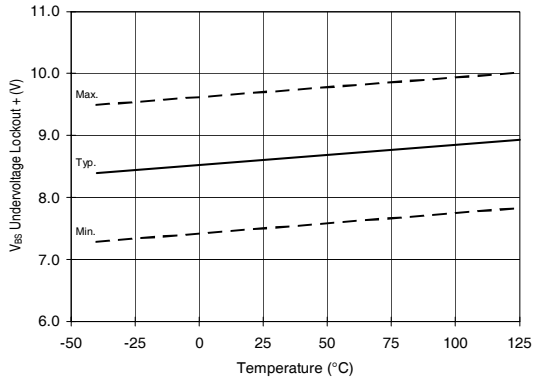


Figure 22.  $V_{BS}$  Undervoltage (+) vs. Temperature

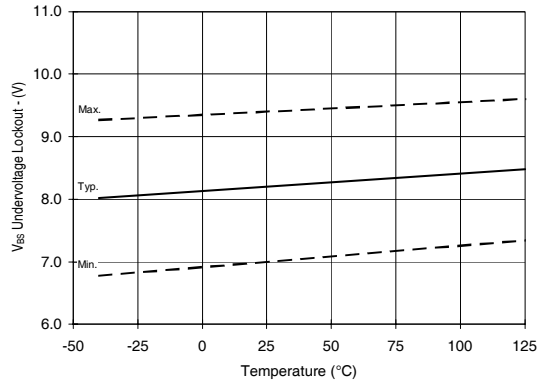


Figure 23.  $V_{BS}$  Undervoltage (-) vs. Temperature

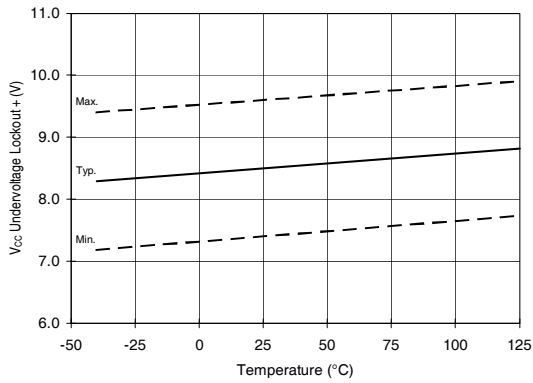


Figure 24.  $V_{CC}$  Undervoltage (+) vs. Temperature

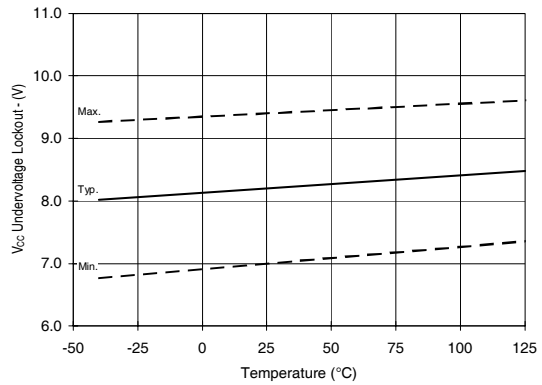


Figure 25.  $V_{CC}$  Undervoltage (-) vs. Temperature

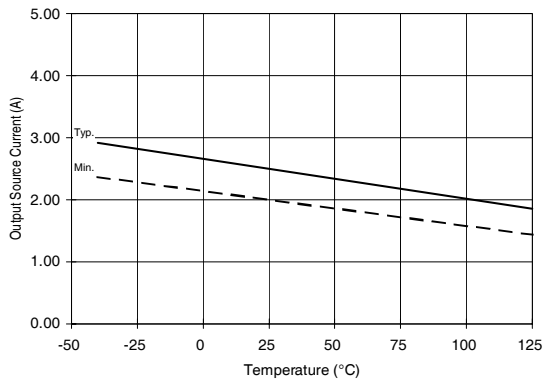


Figure 26A. Output Source Current vs. Temperature

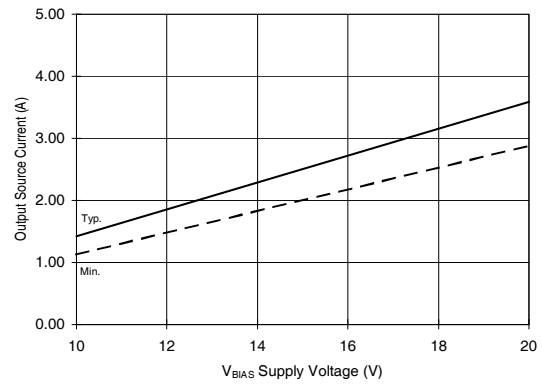


Figure 26B. Output Source Current vs. Voltage

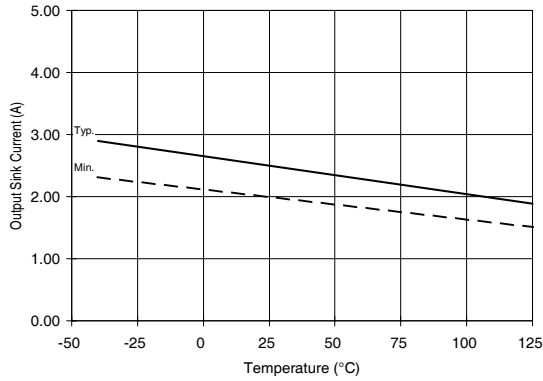


Figure 27A. Output Sink Current vs. Temperature

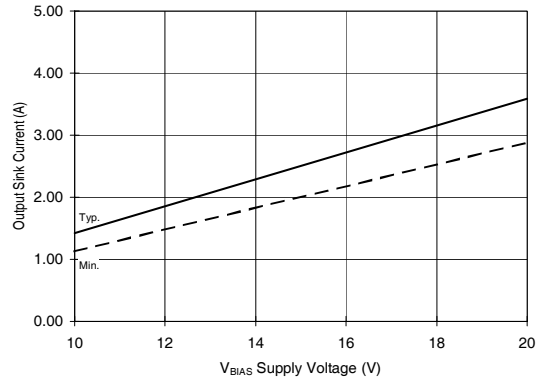


Figure 27B. Output Sink Current vs. Voltage

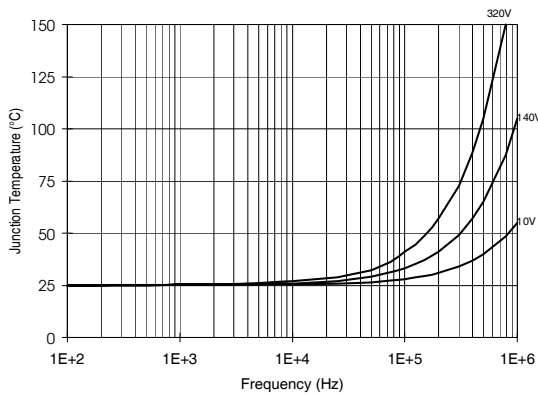


Figure 28. IR2110  $T_J$  vs. Frequency (IRFBC20)  
 $R_{GATE} = 33W, V_{CC} = 15V$

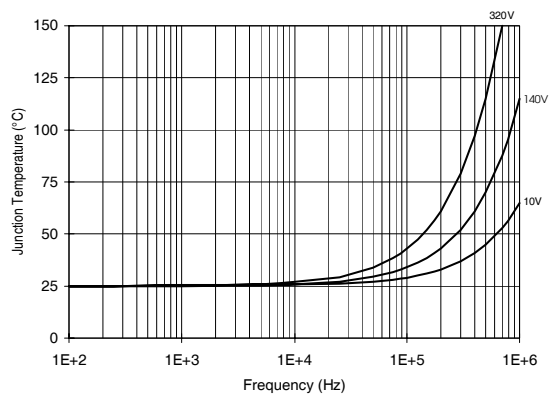


Figure 29. IR2110  $T_J$  vs. Frequency (IRFBC30)  
 $R_{GATE} = 22W, V_{CC} = 15V$

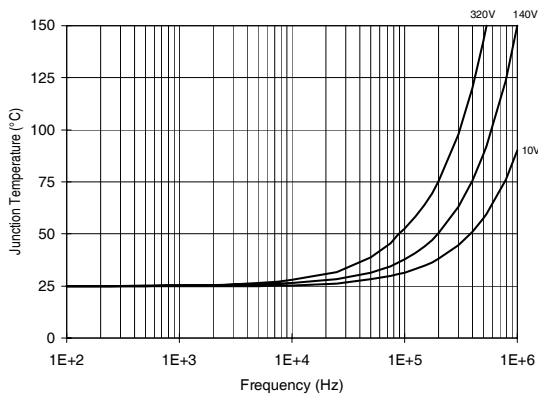


Figure 30. IR2110  $T_J$  vs. Frequency (IRFBC40)  
 $R_{GATE} = 15W, V_{CC} = 15V$

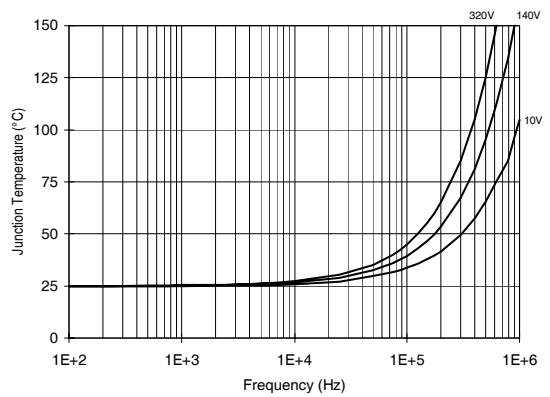


Figure 31. IR2110  $T_J$  vs. Frequency (IRFPE50)  
 $R_{GATE} = 10W, V_{CC} = 15V$

# IR2110E4

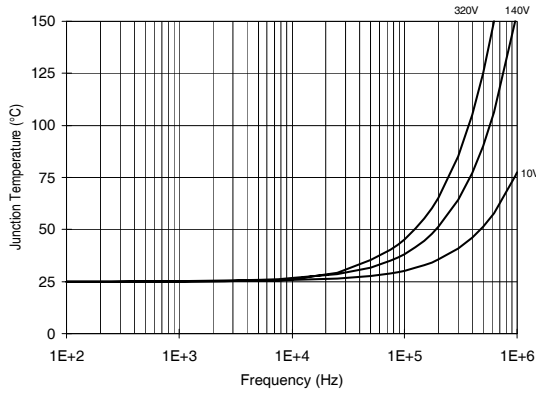


Figure 32. IR2110S  $T_J$  vs. Frequency (IRFBC20)  
 $R_{GATE} = 33W, V_{CC} = 15V$

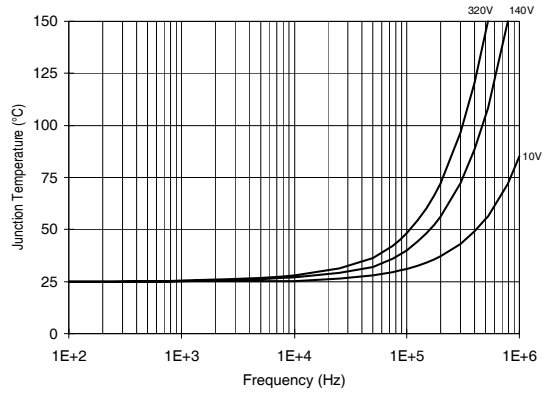


Figure 33. IR2110S  $T_J$  vs. Frequency (IRFBC30)  
 $R_{GATE} = 22W, V_{CC} = 15V$

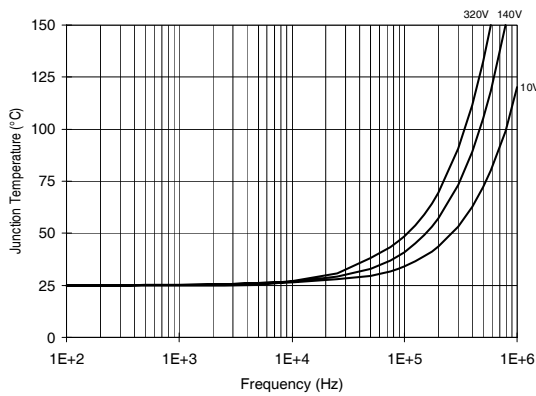


Figure 34. IR2110S  $T_J$  vs. Frequency (IRFBC40)  
 $R_{GATE} = 15W, V_{CC} = 15V$

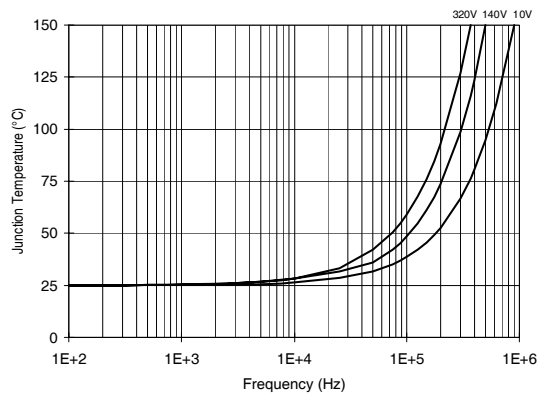


Figure 35. IR2110S  $T_J$  vs. Frequency (IRFPE50)  
 $R_{GATE} = 10W, V_{CC} = 15V$

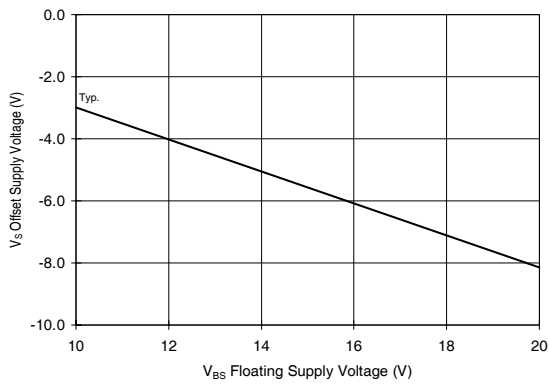


Figure 36. Maximum  $V_S$  Negative Offset vs.  $V_{BS}$  Supply Voltage

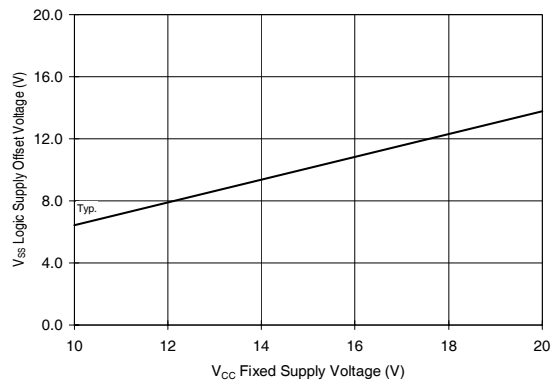
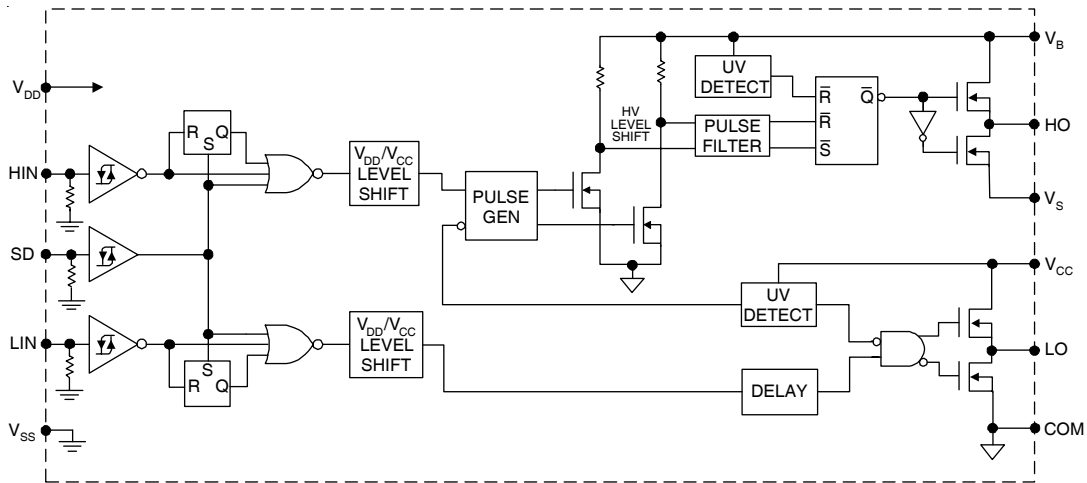


Figure 37. Maximum  $V_{SS}$  Positive Offset vs.  $V_{CC}$  Supply Voltage

**Functional Block Diagram**



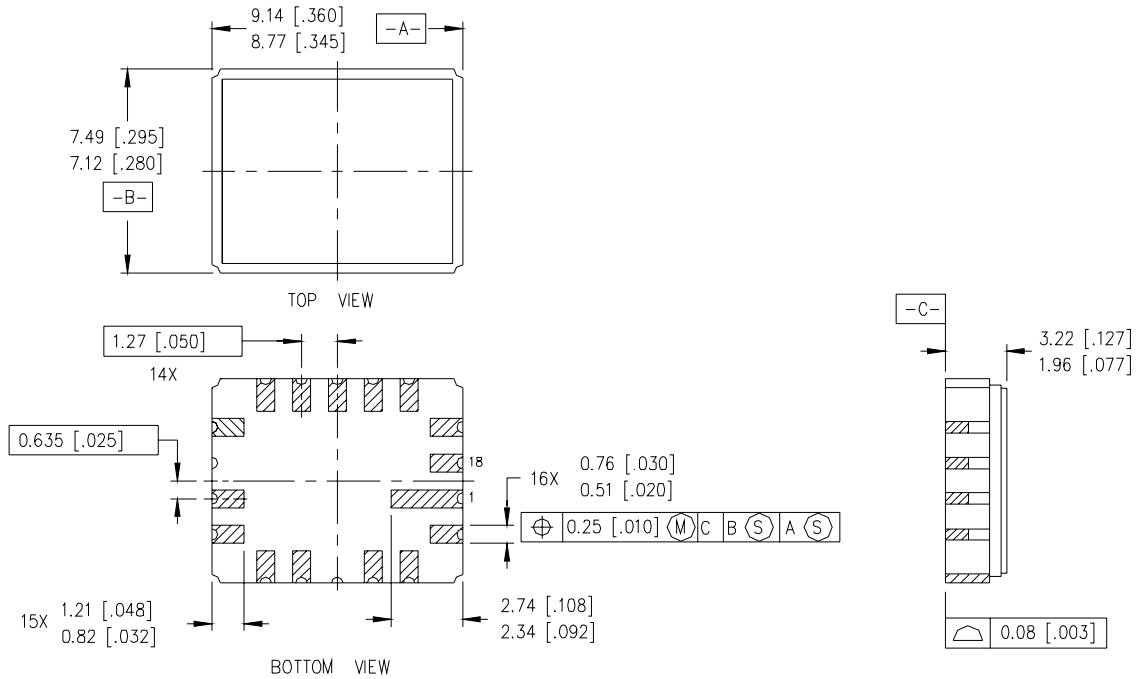
**Lead Definitions**

Lead	
Symbol	Description
V <sub>DD</sub>	Logic supply
HIN	Logic input for high side gate driver output (HO), in phase
SD	Logic input for shutdown
LIN	Logic input for low side gate driver output (LO), in phase
V <sub>SS</sub>	Logic ground
V <sub>B</sub>	High side floating supply
HO	High side gate drive output
V <sub>S</sub>	High side floating supply return
V <sub>CC</sub>	Low side supply
LO	Low side gate drive output
COM	Low side return

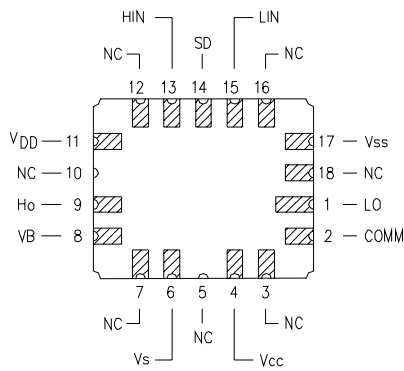
# IR2110E4

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## Case Outline and Dimensions — Leadless Chip Carrier (LCC-18) Package



### PAD ASSIGNMENTS



### NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

**IR LEOMINSTER :** 205 Crawford St., Leominster, Massachusetts 01453, USA Tel: (978) 534-5776

TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.

Data and specifications subject to change without notice. 05/2011